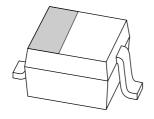
### DISCRETE SEMICONDUCTORS

# DATA SHEET



# BAP65-03 Silicon PIN diode

Product specification
Supersedes data of 2001 May 11

2004 Feb 11





Silicon PIN diode BAP65-03

#### **FEATURES**

- High voltage, current controlled
- RF resistor for RF switches
- Low diode capacitance
- Low diode forward resistance (low loss)
- Very low series inductance.

#### **APPLICATIONS**

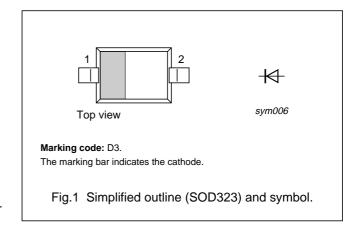
- · RF attenuators and switches
- · Bandswitch for TV tuners
- Series diode for mobile communication transmit/receive switch.

#### **DESCRIPTION**

Planar PIN diode in a SOD323 small SMD plastic package.

#### **PINNING**

PIN	DESCRIPTION
1	cathode
2	anode



#### **ORDERING INFORMATION**

TYPE		PACKAGE				
NUMBER	NAME	DESCRIPTION	VERSION			
BAP65-03	_	plastic surface mounted package; 2 leads	SOD323			

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>R</sub>	continuous reverse voltage		_	30	V
I <sub>F</sub>	continuous forward current		_	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>s</sub> ≤ 90 °C	_	500	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-65	+150	°C

Silicon PIN diode BAP65-03

#### **ELECTRICAL CHARACTERISTICS**

 $T_i = 25$  °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 50 mA	0.9	1.1	V
I <sub>R</sub>	reverse leakage current	V <sub>R</sub> = 20 V	_	20	nA
C <sub>d</sub>	diode capacitance	V <sub>R</sub> = 0 V; f = 1 MHz	0.65	_	pF
		V <sub>R</sub> = 1 V; f = 1 MHz	0.55	0.9	pF
		V <sub>R</sub> = 3 V; f = 1 MHz	0.5	0.8	pF
		V <sub>R</sub> = 20 V; f = 1 MHz	0.375	_	pF
r <sub>D</sub>	diode forward resistance	I <sub>F</sub> = 1 mA; f = 100 MHz	1	_	Ω
		I <sub>F</sub> = 5 mA; f = 100 MHz; note 1	0.65	0.95	Ω
		I <sub>F</sub> = 10 mA; f = 100 MHz; note 1	0.56	0.9	Ω
		I <sub>F</sub> = 100 mA; f = 100 MHz	0.35	_	Ω
S <sub>21</sub>   <sup>2</sup>	isolation	V <sub>R</sub> = 0; f = 900 MHz	10.2	_	dB
		V <sub>R</sub> = 0; f = 1800 MHz	5.8	_	dB
		V <sub>R</sub> = 0; f = 2450 MHz	4.1	_	dB
S <sub>21</sub>   <sup>2</sup>	insertion loss	I <sub>F</sub> = 1 mA; f = 900 MHz	0.1	_	dB
		I <sub>F</sub> = 1 mA; f = 1800 MHz	0.14	_	dB
		I <sub>F</sub> = 1 mA; f = 2450 MHz	0.18	_	dB
s <sub>21</sub>   <sup>2</sup>	insertion loss	$I_F = 5 \text{ mA}; f = 900 \text{ MHz}$	0.06	_	dB
		I <sub>F</sub> = 5 mA; f = 1800 MHz	0.1	_	dB
		I <sub>F</sub> = 5 mA; f = 2450 MHz	0.14	_	dB
S <sub>21</sub>   <sup>2</sup>	insertion loss	I <sub>F</sub> = 10 mA; f = 900 MHz	0.06	_	dB
		I <sub>F</sub> = 10 mA; f = 1800 MHz	0.1	_	dB
		I <sub>F</sub> = 10 mA; f = 2450 MHz	0.13	_	dB
S <sub>21</sub>   <sup>2</sup>	insertion loss	I <sub>F</sub> = 100 mA; f = 900 MHz	0.05	_	dB
		I <sub>F</sub> = 100 mA; f = 1800 MHz	0.1	_	dB
		I <sub>F</sub> = 100 mA; f = 2450 MHz	0.14	_	dB
τ∟	charge carrier life time	when switched from I <sub>F</sub> = 10 mA to I <sub>R</sub> = 6 mA; R <sub>L</sub> = 100 $\Omega$ ; measured at I <sub>R</sub> = 3 mA	0.17	_	μs
L <sub>S</sub>	series inductance	I <sub>F</sub> = 100 mA; f = 100 MHz	1.5	_	nH
	II.				

#### Note

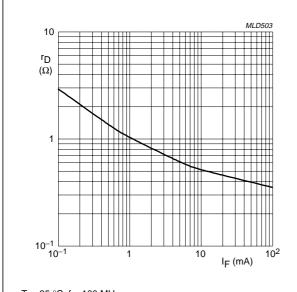
1. Guaranteed on AQL basis: inspection level S4, AQL 1.0.

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R <sub>th(j-s)</sub>	thermal resistance from junction to soldering point	120	K/W

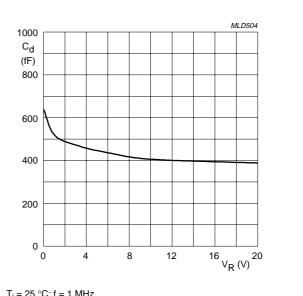
#### Silicon PIN diode **BAP65-03**

#### **GRAPHICAL DATA**



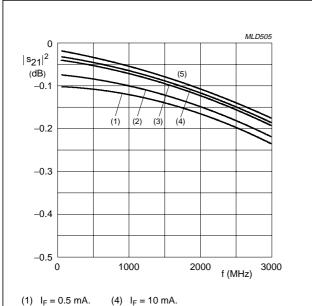
 $T_i = 25$  °C; f = 100 MHz.

Fig.2 Forward resistance as a function of forward current; typical values.



 $T_j = 25$  °C; f = 1 MHz.

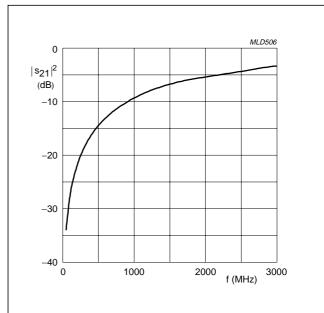
Diode capacitance as a function of reverse voltage; typical values.



- (2)  $I_F = 1 \text{ mA}.$
- (3)  $I_F = 5 \text{ mA}.$
- (5)  $I_F = 100 \text{ mA}.$

Diode inserted in series with a 50  $\Omega$  stripline circuit and biased via the analyzer Tee network;  $T_{amb} = 25$  °C.

Fig.4 Insertion loss  $(|s_{21}|^2)$  of the diode as a function of frequency; typical values.



Diode zero biased and inserted in series with a 50  $\Omega$  stripline circuit.  $T_{amb} = 25 \, ^{\circ}C.$ 

Fig.5 Isolation ( $|s_{21}|^2$ ) of the diode as a function of frequency; typical values.

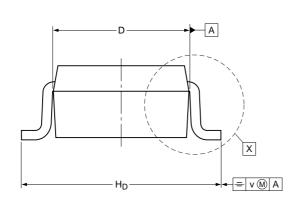
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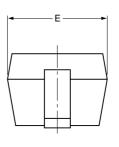
Silicon PIN diode BAP65-03

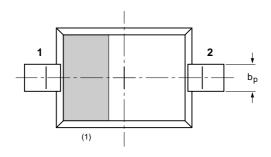
#### **PACKAGE OUTLINE**

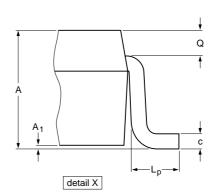
#### Plastic surface mounted package; 2 leads

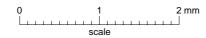
SOD323











#### DIMENSIONS (mm are the original dimensions)

UNIT	Α	A <sub>1</sub> max	bp	С	D	E	H <sub>D</sub>	Lp	Q	v
mm	1.1 0.8	0.05	0.40 0.25	0.25 0.10	1.8 1.6	1.35 1.15	2.7 2.3	0.45 0.15		0.2

#### Note

1. The marking bar indicates the cathode

OUTLINE		REFERENCES				ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOD323			SC-76			<del>99-09-13</del> 03-12-17

Silicon PIN diode BAP65-03

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LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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